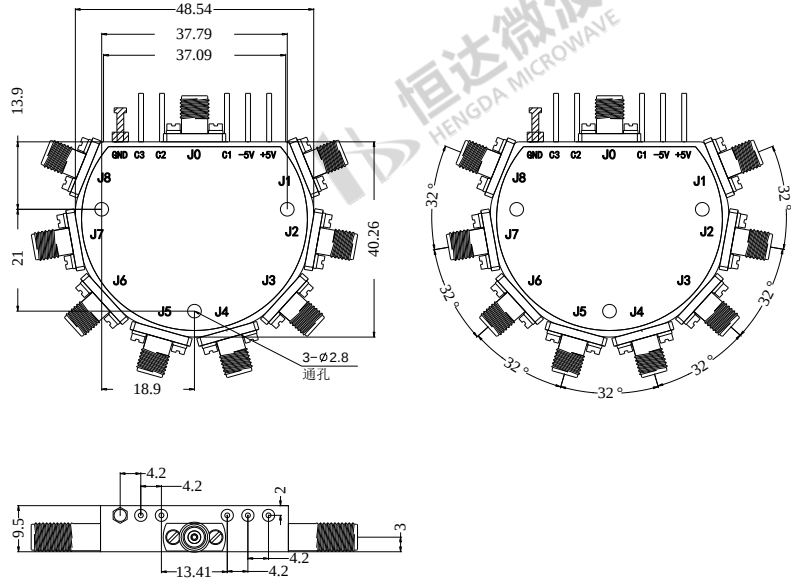
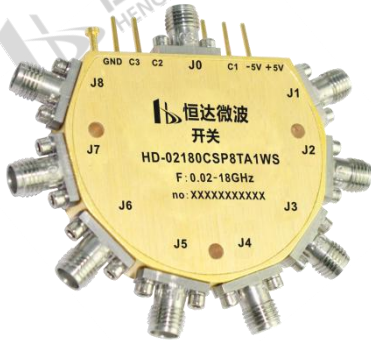


产品名称：射频吸收开关

产品型号：HD-02180CSP8TA1WS



2. 详细技术参数 (*为主要参数)

参 数	最小值	典型值	最大值	最小值	典型值	最大值	最小值	典型值	最大值	单位
频率范围	0.02-6		6-12		12-18					GHz
插损		2.5	4.5		3.8	5.5		5.5	6.0	dB
插损/温度平衡度		0.003			0.003			0.003		dB/ ° C
隔离度	60	85		75	80		60	70		dB
输入驻波比		1.5	1.8		1.5	1.8		1.5	2	: 1
输出驻波比		1.5	1.8		1.5	1.8		1.5	2	: 1
射频输入功率 (CW)			30			30			30	dBm
直流功耗		1.5			1.5			1.5		W
0.1dB压缩点		30			30			30		dBm
输入三阶截获点		55			55			55		dBm
开关速度			250			250			250	ns
重量	50									g
阻抗	50									Ω
偏置电流 (+5V/-5V)	350/50									mA
输入输出连接头	SMA-Female									
表面处理	镀金									
腔体材料	铝									
封装形式	标准封装 (气密封装可选)									

2. 逻辑关系

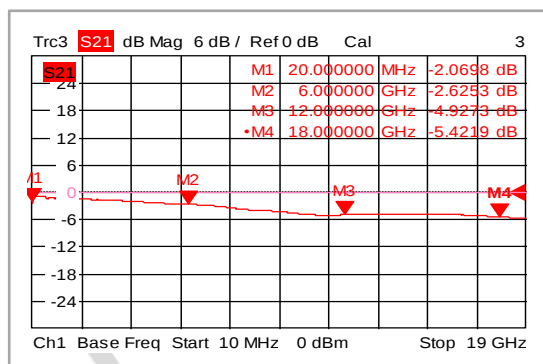
TTL高低电平控制电压			低电压 (0)=0-0.8V
			高电压 (1)=2.8-5V
控制输入TTL			信号通断状态
C3	C2	C1	
0	0	0	J0-J1
0	0	1	J0-J2
0	1	0	J0-J3
0	1	1	J0-J4
1	0	0	J0-J5
1	0	1	J0-J6
1	1	0	J0-J7
1	1	1	J0-J8
控制方式可按需求定制 (TTL控制、USB控制、MICRO-D控制、LAN网络控制)			

3. 额定参数与环境

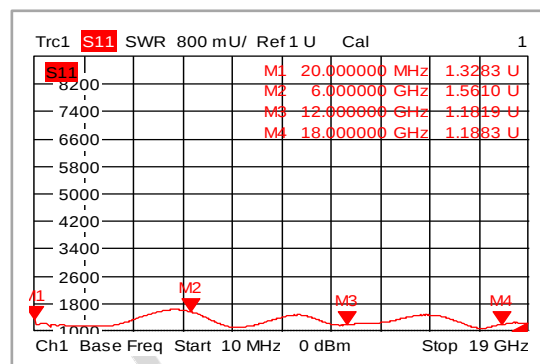
偏置电压	+5V±10%/-5V±10%
工作温度	-45°C~+85°C
存储温度	-55°C~+125°C
海拔高度	762米 (环氧树脂密封条件)
	1524米. 最小1个标准大气压 (气密封装条件) (可选)
注:TTL引脚不能接负压, 否则会损坏内部驱动器。	

4. 产品测试图

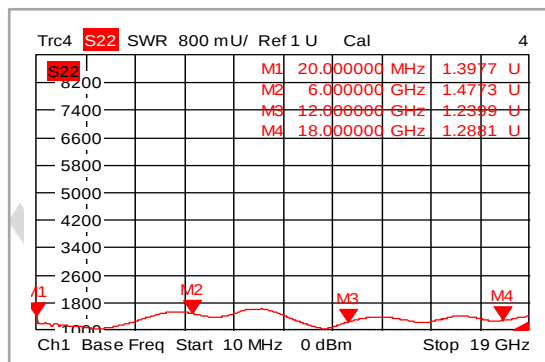
损耗 (+25°C)



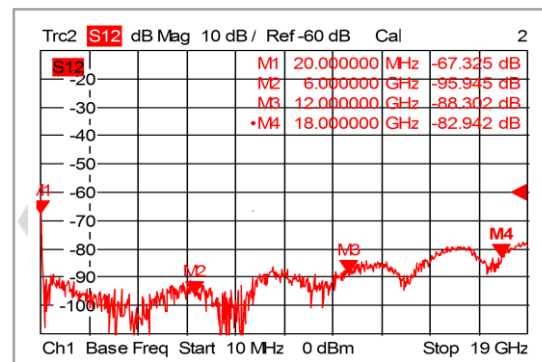
输入驻波比 (+25°C)



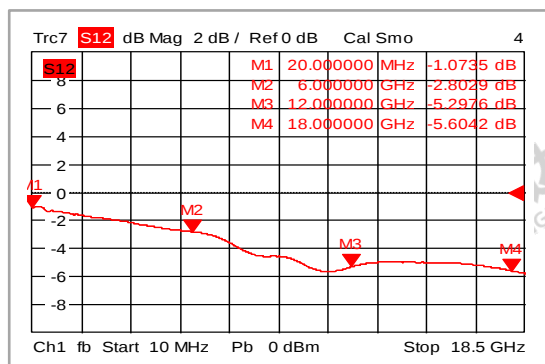
输出驻波比 (+25℃)



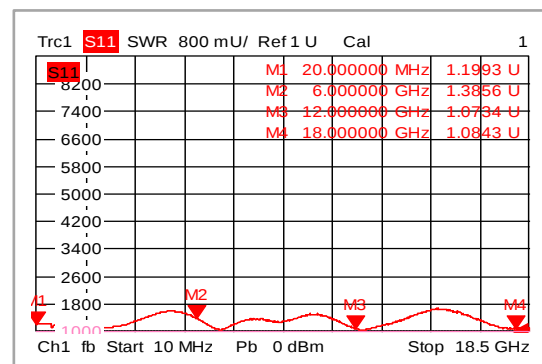
隔离度 (+25℃)



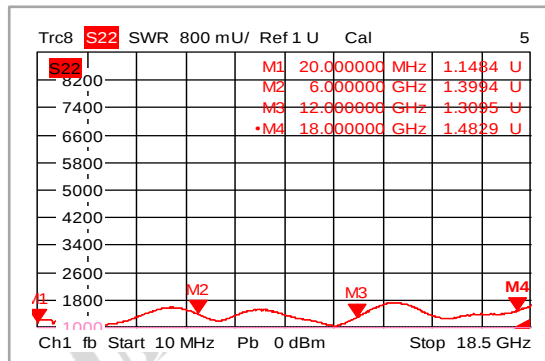
损耗 (-45℃)



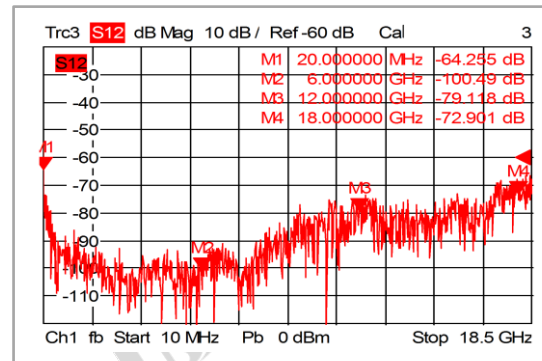
输入驻波比 (-45℃)



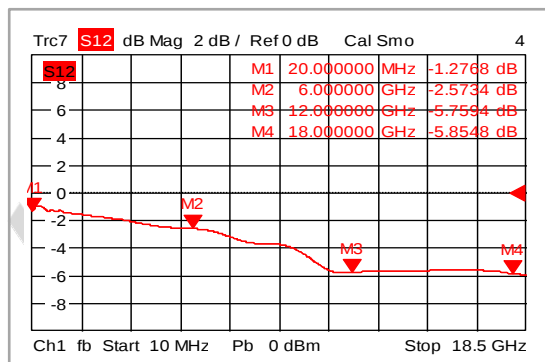
输出驻波比 (-45℃)



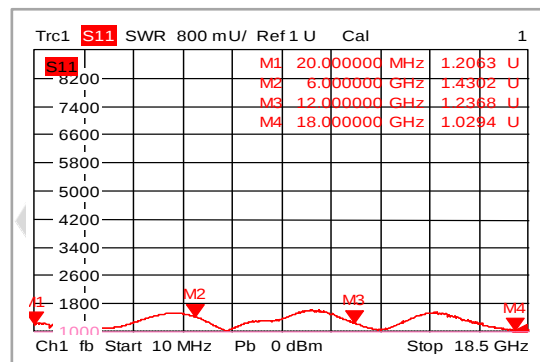
隔离度 (-45℃)



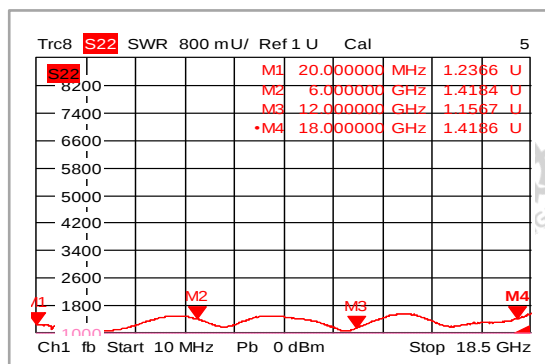
损耗 (+85℃)



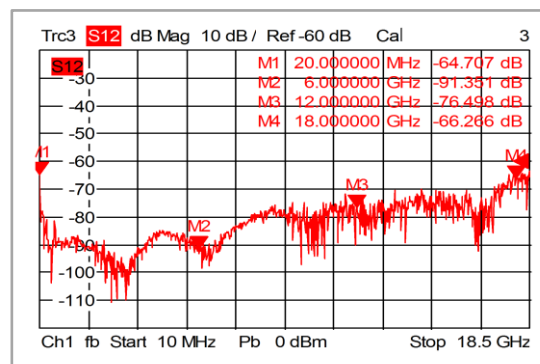
输入驻波比 (+85℃)



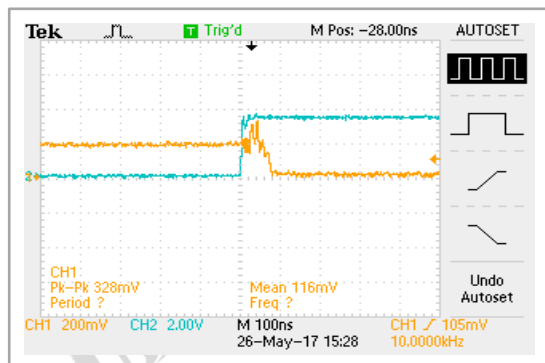
输出驻波比 (+85℃)



隔离度 (+85℃)



开关速度



开关速度

